Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 - 33. (Cancelled).

34. (Currently Amended) A vapor deposition apparatus for use in depositing an organic EL layer, the vapor deposition apparatus comprising:

a process chamber for carrying out vapor deposition on a substrate;

a substrate introducing chamber connected to the process chamber through a gate valve;

a substrate introducing door connected to the substrate introducing chamber;

a deposition source chamber connected to the process chamber and having a deposition source container;

a shutter mechanism between the deposition source chamber and the process chamber;

a first primary pump connected to the process chamber through a pump gate valve;

a first gasket placed between the substrate introducing door and the substrate introducing chamber;

a second gasket placed between the substrate introducing chamber and the process chamber;

a third gasket placed between the first primary pump and the process chamber;

a fourth gasket placed between the process chamber and the shutter mechanism; and

a fifth gasket placed between the shutter mechanism and the deposition source chamber,

wherein:

the first gasket and the fifth gasket are formed by a perfluoroelastomer, [[and]]

the second, third, and fourth gaskets are formed by metal or ceramic, and

the deposition source container accommodates an organic material for the organic EL layer and has an inner surface having center line average roughness not greater than 100 nm.

35. (Previously Presented) The vapor deposition apparatus according to claim 34, further comprising a sixth gasket placed between the substrate introducing chamber and a second primary pump, the sixth gasket being formed by metal or ceramic.

36. (Previously Presented) The vapor deposition apparatus according to claim 34, wherein the deposition source container is made of alumina.

37. (Currently Amended) The vapor deposition apparatus according to claim 36, wherein the ~~deposition source container has an inner surface substantially flat by polishing~~ center line average roughness is not greater than 10 nm.

38. (Previously Presented) The vapor deposition apparatus according to claim 34, wherein the second, third, and fourth gaskets are formed by copper.

39. (Previously Presented) The vapor deposition apparatus according to claim 34, wherein the first gasket has been subjected to a process of contacting it with water at 80°C or more.

40. (Previously Presented) The vapor deposition apparatus according to claim 34, further comprising:

a first secondary pump connected to an exhaust side of the first primary pump; and

a gas introducing portion for introducing an inert gas between the first primary pump and the first secondary pump.

41. (Previously Presented) The vapor deposition apparatus according to claim 35, further comprising:

a second secondary pump connected to an exhaust side of the second primary pump; and

a gas introducing portion for introducing an inert gas between the second primary pump and the second secondary pump.

42. (Withdrawn) A method of depositing an organic emitting layer (EL) onto a substrate, using a vapor deposition apparatus according to claim 34, comprising evaporating an organic EL element material contained in the deposition source container to a substrate placed in the process chamber.

43. (Withdrawn) The method according to claim 42, wherein a process pressure is 100 Torr or less.